Product data sheet

1. Product profile

1.1 General description

10 W LDMOS power transistor for base station applications at frequencies from HF to 1000 MHz.

Table 1. Typical performance

RF performance at $T_h = 25$ °C in a common source test circuit.

Mode of operation	f		I _{DQ}	_	G _p	η _D	d _{im}
	(MHz)	(V)	(mA)	(VV)	(dB)	(%)	(dBc)
CW, 2-tone, class-AB	$f_1 = 960; f_2 = 960.1$	26	85	10 (PEP)	18.5	40	≤-31
CW, 1-tone, class-AB	f = 960	26	85	10	18.5	52	-

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Typical 2-tone performance at a supply voltage of 26 V and I_{DQ} of 85 mA
 - Output power = 10 W (PEP)
 - ◆ Gain = 18.5 dB
 - ◆ Efficiency = 40%
 - ♦ d_{im} = -31 dBc
- Easy power control
- Excellent ruggedness
- High power gain
- Excellent thermal stability
- Designed for broadband operation (HF to 1000 MHz)
- No internal matching for broadband operation
- SMD package.

1.3 Applications

- RF power amplifiers for GSM, EDGE and CDMA base stations and multicarrier applications in the 800 to 1000 MHz frequency range
- Broadcast drivers.



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2. Pinning information

Table 2. Pinning

Idolo Li	9		
Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate		1
3	source, connected to flange	3	2 — — 3 3 sym112

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BLF1043	-	ceramic surface mounted package; 2 leads	SOT538A			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-	±15	V
I _D	drain current (DC)		-	2.2	Α
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th j-h}	thermal resistance from junction to heatsink	$T_{mb} = 25 ^{\circ}C$	<u>[1]</u> 9	K/W

^[1] Thermal resistance is determined under RF operating conditions. Typical value with device soldered on PC board with 32 via holes (diameter 0.3 mm) and thermal compound between PCB and heatsink.

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6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0; I_D = 0.2 \text{ mA}$	65	-	-	V
V_{GSth}	gate-source threshold voltage	$V_{DS} = 10 \text{ V; } I_{D} = 20 \text{ mA}$	4	-	5	V
I _{DSS}	drain-source leakage current	V _{GS} = 0; V _{DS} = 26 V	-	-	1.5	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 9$ V; $V_{DS} = 10$ V	2.8	-	-	Α
I _{GSS}	gate leakage current	$V_{GS} = \pm 15 \text{ V};$ $V_{DS} = 0$	-	-	40	nA
9fs	forward transconductance	$V_{DS} = 10 \text{ V; } I_{D} = 0.75 \text{ A}$	-	0.5	-	S
R _{DSon}	drain-source on-state resistance	$V_{DS} = 10 \text{ V; } I_D = 0.75 \text{ A}$	-	1.05	-	Ω
C _{iss}	input capacitance	V _{GS} = 0; V _{DS} = 26 V; f = 1 MHz	-	11	-	pF
C _{oss}	output capacitance	V _{GS} = 0; V _{DS} = 26 V; f = 1 MHz	-	9	-	pF
C _{rss}	feedback capacitance	V _{GS} = 0; V _{DS} = 26 V; f = 1 MHz	-	0.5	-	pF

7. Application information

Table 7. RF performance in a common source class-AB circuit

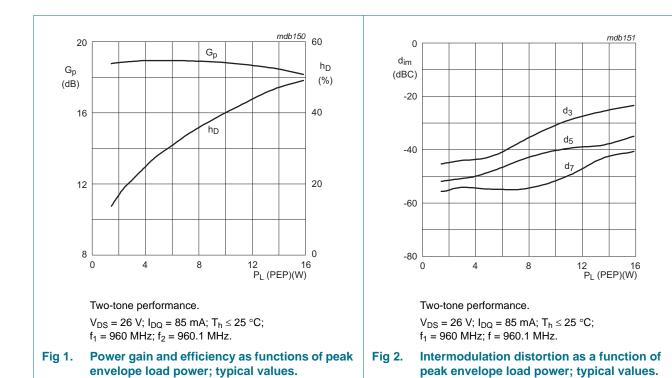
 T_h = 25 °C; $R_{th\,j\text{-}h}$ = 9 K/W, unless otherwise specified.

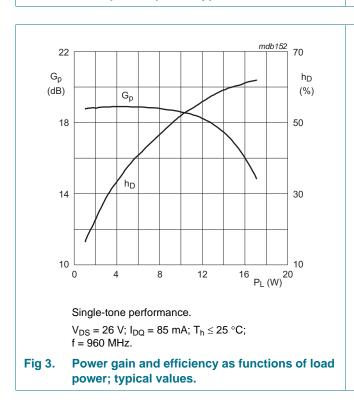
Mode of operation	f	V _{DS}	I _{DQ}	P _L	G _p	η _D	d _{im}
	(MHz)	(V)	(mA)	(W)	(dB)	(%)	(dBc)
CW, 2-tone, class-AB	$f_1 = 960; f_2 = 960.1$	26	85	10 (PEP)	>16.5	>38	≤-25

7.1 Ruggedness in class-AB operation

The BLF1043 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 26 V; f = 960 MHz at rated load power.

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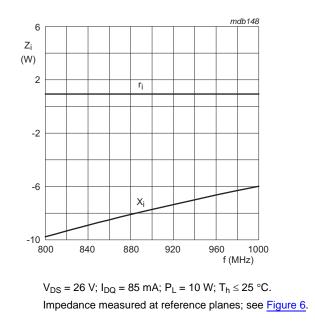
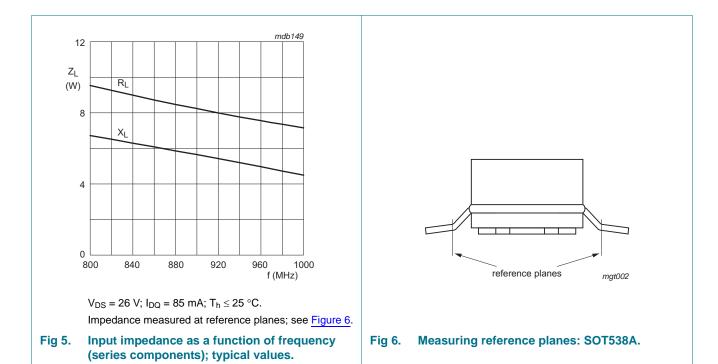
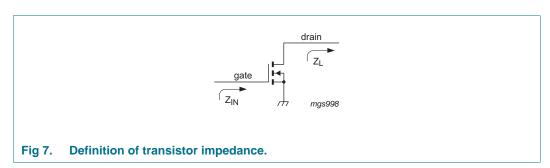
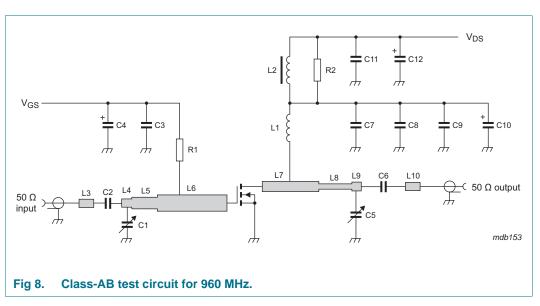


Fig 4. Input impedance as a function of frequency (series components); typical values.

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8. Test information

Table 8. List of components (see Figure 8 and Figure 9)

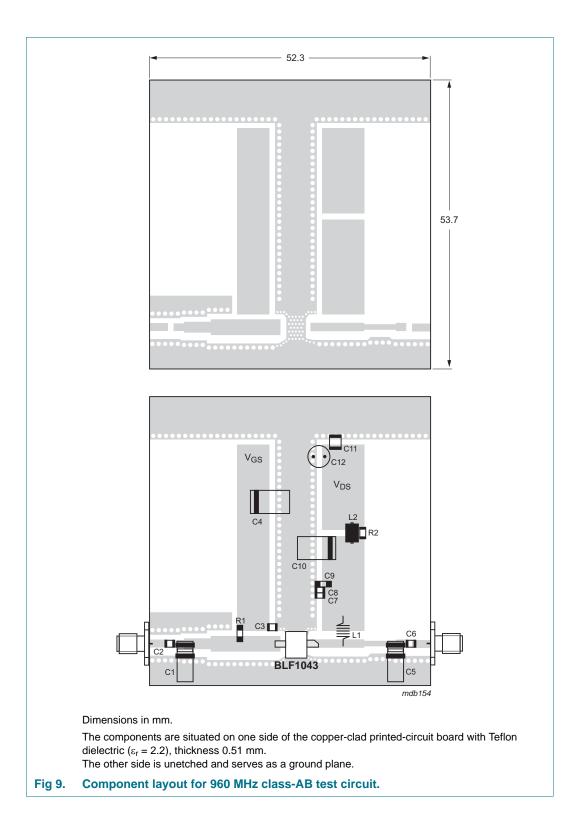
Component	Description		Value	Dimension	Catalogue no.
C1, C5	Tekelec variable capacitor		0.8 to 8 pF		
C2, C3, C6, C7	multilayer ceramic chip capacitor	[1]	56 pF		
C4, C10	tantalum SMD capacitor		10 μF; 35 V		
C8	multilayer ceramic chip capacitor	[1]	1 nF		
C9	multilayer ceramic chip capacitor		100 nF		2222 581 16641
C11	multilayer ceramic chip capacitor	[2]	1 nF		
C12	electrolytic capacitor		100 μF; 63 V		2222 037 58101
L1	3 turns enamelled 0.5 mm copper wire			3 loops; d = 3.5 mm	
L2	ferrite bead; ferroxcube CBD4.6/3/3-4S2				
L3	stripline	[3]	50 Ω	3.5 x 1.5 mm	
L4	stripline	[3]	50 Ω	2 x 1.5 mm	
L5	stripline	[3]	42 Ω	5 x 2 mm	
L6	stripline	[3]	31 Ω	13 x 3 mm	
L7	stripline	[3]	50 Ω	10 x 1.5 mm	
L8	stripline	[3]	65 Ω	5.9 x 1 mm	
L9	stripline	[3]	50 Ω	2 x 1.5 mm	
L10	stripline	[3]	50 Ω	3.5 x 1.5 mm	
R1	metal film resistor		39 Ω, 0.6 W		
R2	metal film resistor		10 Ω, 0.6 W		2322 256 11009

^[1] American Technical Ceramics type 100A or capacitor of same quality.

^[2] American Technical Ceramics type 100B or capacitor of same quality.

^[3] The striplines are on a double copper-clad printed-circuit board with Rogers 5880 dielectric ($\epsilon_r = 2.2$); thickness 0.51 mm.

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9. Package outline

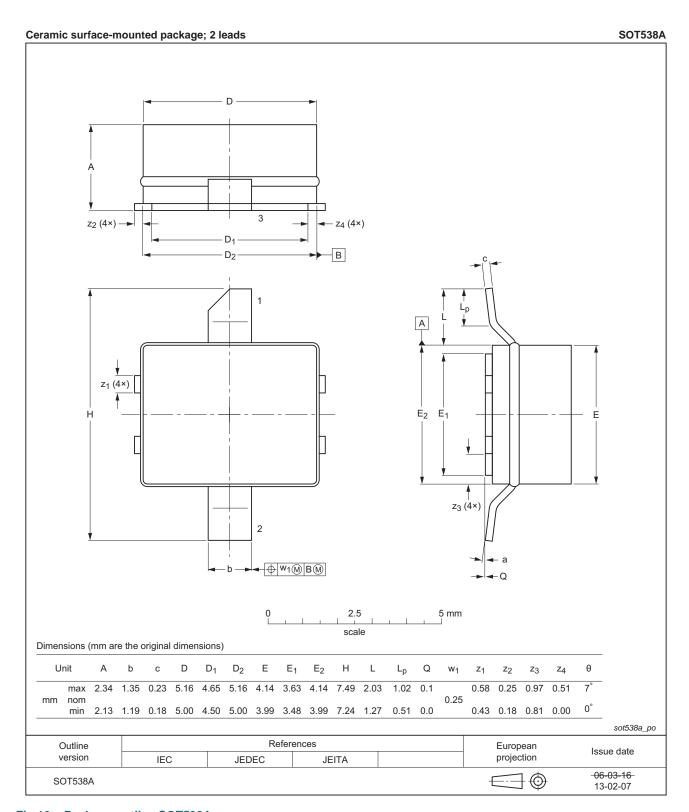


Fig 10. Package outline SOT538A

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10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF1043 v.8	20130506	Product data sheet	-	BLF1043 v.7
Modifications:	 The format of this data sheet has been reguidelines of NXP Semiconductors. Legal texts have been adapted to the new Package outline drawings have been upon 		new company name whe	re appropriate.
BLF1043 v.7	20030313	Product specification	-	BLF1043 v.6

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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